





FZT1051A

40V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

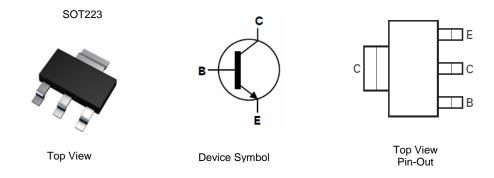
- BV_{CEO} > 40V
- I_C = 5A High Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 120mV @ 1A
- $R_{SAT} = 50 m\Omega$ @ 5A for a Low Equivalent On-Resistance
- h_{FE} Specified up to 10A for a High Gain Hold-Up
- Complementary PNP Type: FZT1151A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)

Applications

- Solenoid, Relay and Actuator Drivers
- DC Modules
- Motor Control



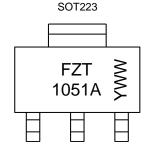
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1051ATA	AEC-Q101	FZT1051A	7	12	1,000
FZT1051ATC	AEC-Q101	FZT1051A	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 1051A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	5	Α
Peak Pulse Current	Ісм	10	Α
Base Current	Ι _Β	1	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	ь	2.0	W	
Power Dissipation	(Note 7)	P _D	1.6	VV	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ heta JL}$	10.9		
Operating and Storage Temperature Range	T_{J} , T_{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

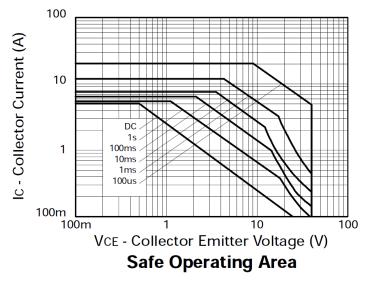
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

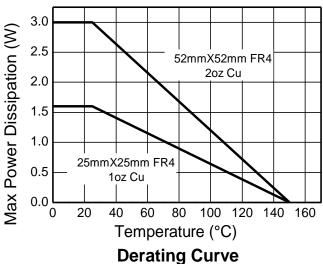
Notes:

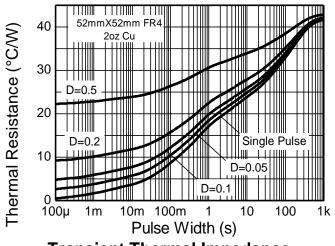
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 Same as Note 5, except the device is mounted on minimum recommended pad layout.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

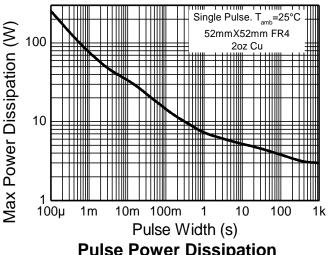


Thermal Characteristics and Derating Information









Pulse Power Dissipation





FZT1051A

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	190	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CES}	150	190	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CEV}	150	190	_	V	$I_C = 100\mu A, V_{EB} = 1V$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	40	60	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	$I_E = 100\mu A$
Collector Cut-Off Current	I _{CBO}	_ _	<1 -	10 0.5	nΑ μΑ	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Collector Cut-Off Current	I _{CES}	-	<1	10	nA	V _{CB} = 120V
Emitter Cut-Off Current	I _{EBO}	_	<1	10	nA	V _{EB} = 6V
	VCE(sat)	-	17	25	mV	$I_C = 200 \text{mA}, I_B = 10 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)		-	85	120		$I_C = 1A$, $I_B = 10mA$
Collector-Entitler Saturation voltage (Note 11)		-	140	180		$I_C = 2A$, $I_B = 20mA$
		_	250	340		$I_C = 5A$, $I_B = 100mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	980	1100	mV	$I_C = 5A$, $I_B = 100mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	_	915	1000	mV	$I_C = 5A$, $V_{CE} = 2V$
		290	440	_		$I_C = 10$ mA, $V_{CE} = 2$ V
DC Current Gain (Note 11)	h	270	450	1200		$I_C = 1A$, $V_{CE} = 2V$
DC Current Gain (Note 11)	h _{FE}	130	220	_	_	$I_C = 5A$, $V_{CE} = 2V$
		40	55	_		$I_C = 10A, V_{CE} = 2V$
Output Capacitance	C_obo	_	27	40	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	-	155	-	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
Switching Times	t _{on}	=	220	-	ns	$I_C = 3A$, $V_{CC} = 10V$,
Switching Times	t _{off}	-	540	_	115	$I_{B1} = -I_{B2} = 30\text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

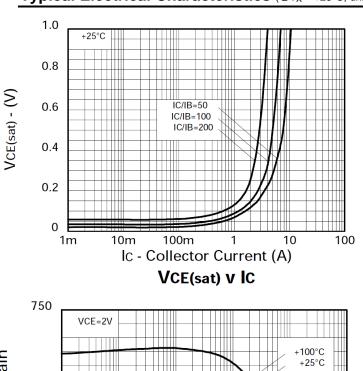


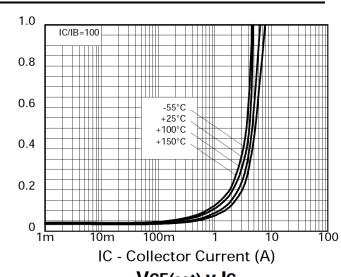
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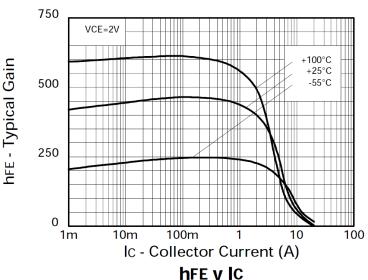
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

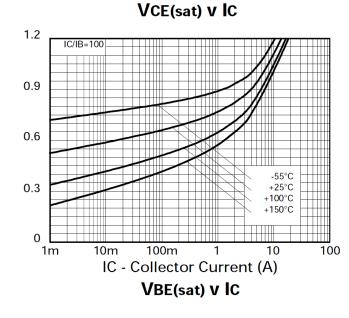
VCE(sat) - (V)

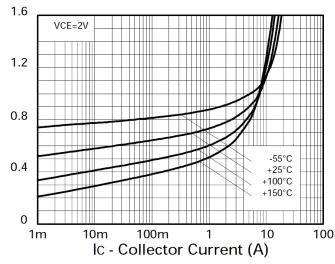
VBE(sat) - (V)







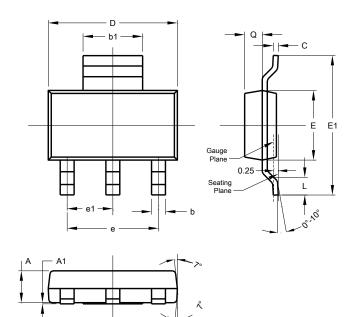






Package Outline Dimensions

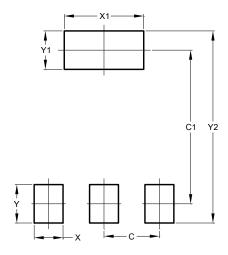
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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